

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

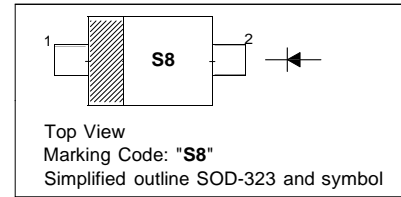
- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

Applications

- High speed switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	30	V
Mean Rectifying Current	I_O	30	mA
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I_{FSM}	200	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$	V_F	-	0.37	V
Reverse Current at $V_R = 30\text{ V}$	I_R	-	0.5	μA
Capacitance Between Terminals at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_T	2	-	pF

Note: ESD sensitive product handling required.

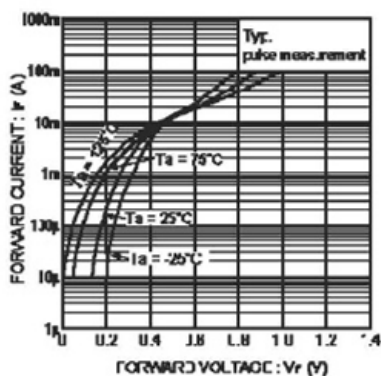


Fig. 1 Forward characteristics

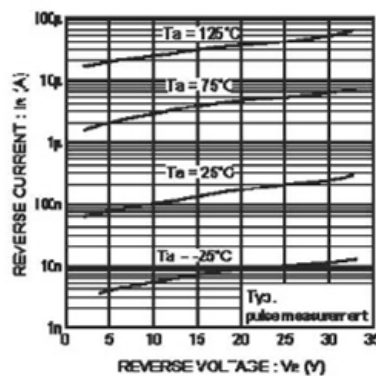


Fig. 2 Reverse characteristics

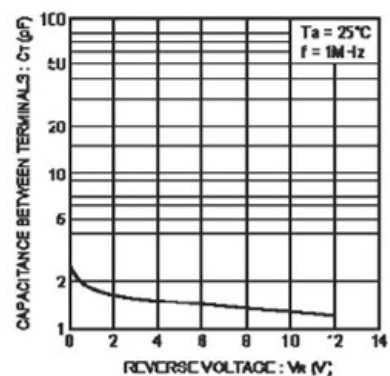
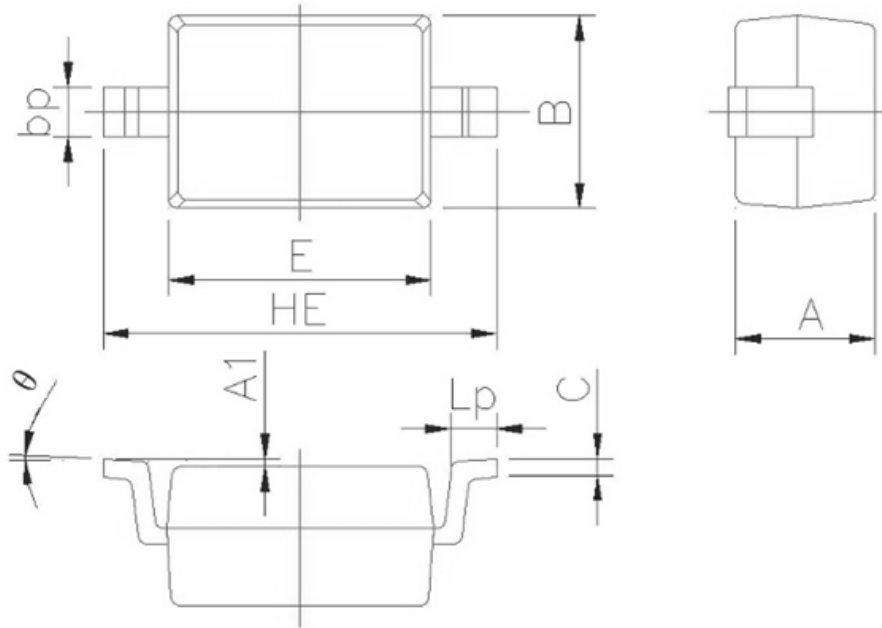


Fig. 3 Capacitance between terminals characteristics

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°